

CORRECTION

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[View Journal](#) | [View Issue](#)Cite this: *RSC Adv.*, 2019, **9**, 3856

DOI: 10.1039/c8ra90105h

www.rsc.org/advances

Correction: All-solution-processed, flexible thin-film transistor based on PANI/PETA as gate/gate insulator

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Correction for 'All-solution-processed, flexible thin-film transistor based on PANI/PETA as gate/gate insulator' by Jin-Yong Hong *et al.*, *RSC Adv.*, 2015, **5**, 105785–105788.

The authors regret the omission of one of the authors, Kyoung-Hwan Shin, from the original manuscript. The corrected author list is as shown above.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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